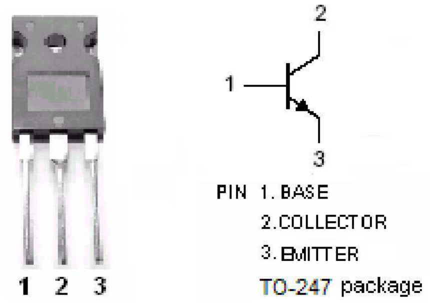
isc Silicon NPN Power Transistor BU2527AW

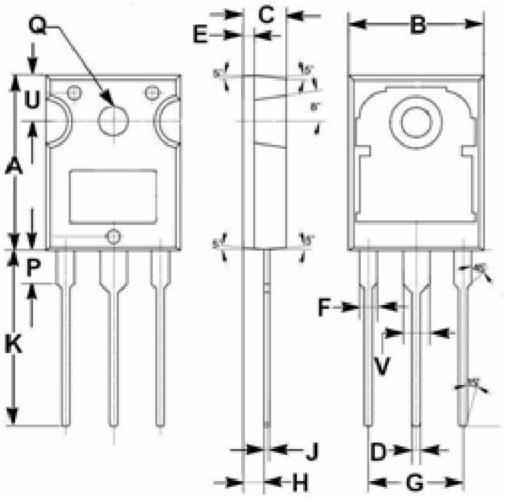


DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= 800V(Min)
- High Switching Speed

APPLICATIONS

- Designed for use in horizontal deflection circuits of high resolution monitors.



DIM	mm MIN	mm MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7.5	V
I_C	Collector Current-Continuous	12	A
I_{CM}	Collector Current-Peak	30	A
I_B	Base Current-Continuous	8	A
I_{BM}	Base Current-Peak	12	A
P_C	Collector Power Dissipation @T_C=25℃	125	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.0	℃/W

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ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 100mA; I_B= 0; L= 25mH	800			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	7.5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 6A ;I_B= 1.2A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 6A ;I_B= 1.2A			1.3	V
I_{CES}	Collector Cutoff Current	V_{CE}=1500V,V_{BE}=0 V_{CE}=1500V,V_{BE}=0;T_C=125℃			0.25 2.0	mA
h_{FE-1}	DC Current Gain	I_C= 1A ; V_{CE}= 5V		10		
h_{FE-2}	DC Current Gain	I_C= 6A ; V_{CE}= 5V	5		9	
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= 10V; f_{test}= 1MHz		145		pF